



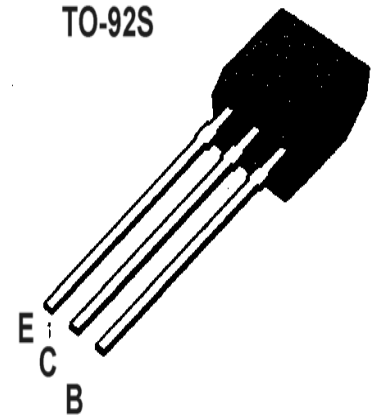
《风光欣》技术资料

2SC2458

NPN EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(TA=25)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current	I _c	150	mA
Collector Dissipation	P _c	200	mW
Junction Temperature	T _j	150	
Storage Temperature	T _{STG}	-55 ~ +150	



ELECTRICAL CHARACTERISTICS(TA=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c = 0.1mA, I _E =0	50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = 1mA, I _B =0	50			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E = 0.1mA, I _c =0	5			V
Collector Cut-off Current	I _{CB0}	V _{CB} =50V, I _E =0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _c =0,			100	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 100mA, I _B =10mA		0.1	0.25	V
DC Current Gain	h _{FE}	V _{CE} = 6V, I _c =2mA,	70		700	
Transition frequency	f _T	V _{CE} = 10V, I _c = 1mA	80			MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V, I _E = 0, f=1MHZ		2	3.5	pF

h_{FE} CLASSIFICATION

Ltem	O	Y	GR	BL
H _{FE}	70-140	120-240	200-400	350-700